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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, IR, POR, PWM, WDT
Number of I/O	26
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 18x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l151g3u3

3.16	Beeper	23
3.17	Communication interfaces	24
3.17.1	SPI	24
3.17.2	I ² C	24
3.17.3	USART	24
3.18	Infrared (IR) interface	24
3.19	Development support	25
4	Pinout and pin description	26
4.1	System configuration options	37
5	Memory and register map	38
5.1	Memory mapping	38
5.2	Register map	39
6	Interrupt vector mapping	57
7	Option bytes	59
8	Unique ID	62
9	Electrical parameters	63
9.1	Parameter conditions	63
9.1.1	Minimum and maximum values	63
9.1.2	Typical values	63
9.1.3	Typical curves	63
9.1.4	Loading capacitor	63
9.1.5	Pin input voltage	64
9.2	Absolute maximum ratings	64
9.3	Operating conditions	66
9.3.1	General operating conditions	66
9.3.2	Embedded reset and power control block characteristics	67
9.3.3	Supply current characteristics	68
9.3.4	Clock and timing characteristics	82
9.3.5	Memory characteristics	88
9.3.6	I/O current injection characteristics	89
9.3.7	I/O port pin characteristics	89

9.3.8	Communication interfaces	97
9.3.9	LCD controller (STM8L152xx only)	102
9.3.10	Embedded reference voltage	103
9.3.11	Temperature sensor	104
9.3.12	Comparator characteristics	104
9.3.13	12-bit DAC characteristics	106
9.3.14	12-bit ADC1 characteristics	108
9.3.15	EMC characteristics	114
10	Package information	116
10.1	ECOPACK	116
10.2	LQFP48 package information	116
10.3	UFQFPN48 package information	120
10.4	LQFP32 package information	123
10.5	UFQFPN32 package information	126
10.6	UFQFPN28 package information	129
10.7	WLCSP28 package information	132
10.8	Thermal characteristics	135
11	Part numbering	136
12	Revision history	137

List of tables

Table 1.	Device summary	1
Table 2.	Medium-density STM8L151x4/6 and STM8L152x4/6 low-power device features and peripheral counts	12
Table 3.	Timer feature comparison	22
Table 4.	Legend/abbreviation for table 5	29
Table 5.	Medium-density STM8L151x4/6, STM8L152x4/6 pin description	29
Table 6.	Flash and RAM boundary addresses	39
Table 7.	Factory conversion registers	39
Table 8.	I/O port hardware register map	39
Table 9.	General hardware register map	40
Table 10.	CPU/SWIM/debug module/interrupt controller registers	55
Table 11.	Interrupt mapping	57
Table 12.	Option byte addresses	59
Table 13.	Option byte description	60
Table 14.	Unique ID registers (96 bits)	62
Table 15.	Voltage characteristics	64
Table 16.	Current characteristics	65
Table 17.	Thermal characteristics	65
Table 18.	General operating conditions	66
Table 19.	Embedded reset and power control block characteristics	67
Table 20.	Total current consumption in Run mode	69
Table 21.	Total current consumption in Wait mode	71
Table 22.	Total current consumption and timing in Low power run mode at VDD = 1.65 V to 3.6 V	74
Table 23.	Total current consumption in Low power wait mode at VDD = 1.65 V to 3.6 V	76
Table 24.	Total current consumption and timing in Active-halt mode at VDD = 1.65 V to 3.6 V	78
Table 25.	Typical current consumption in Active-halt mode, RTC clocked by LSE external crystal	80
Table 26.	Total current consumption and timing in Halt mode at VDD = 1.65 to 3.6 V	80
Table 27.	Peripheral current consumption	81
Table 28.	Current consumption under external reset	82
Table 29.	HSE external clock characteristics	82
Table 30.	LSE external clock characteristics	82
Table 31.	HSE oscillator characteristics	83
Table 32.	LSE oscillator characteristics	84
Table 33.	HSI oscillator characteristics	85
Table 34.	LSI oscillator characteristics	86
Table 35.	RAM and hardware registers	88
Table 36.	Flash program and data EEPROM memory	88
Table 37.	I/O current injection susceptibility	89
Table 38.	I/O static characteristics	90
Table 39.	Output driving current (high sink ports)	93
Table 40.	Output driving current (true open drain ports)	93
Table 41.	Output driving current (PA0 with high sink LED driver capability)	93
Table 42.	NRST pin characteristics	95
Table 43.	SPI1 characteristics	97
Table 44.	I2C characteristics	100
Table 45.	LCD characteristics	102
Table 46.	Reference voltage characteristics	103

4.1 System configuration options

As shown in [Table 5: Medium-density STM8L151x4/6, STM8L152x4/6 pin description](#), some alternate functions can be remapped on different I/O ports by programming one of the two remapping registers described in the “Routing interface (RI) and system configuration controller” section in the STM8L15xxx and STM8L16xxx reference manual (RM0031).

5 Memory and register map

5.1 Memory mapping

The memory map is shown in [Figure 9](#).

Figure 9. Memory map



MS32632V1

1. [Table 6](#) lists the boundary addresses for each memory size. The top of the stack is at the RAM end address.
2. The VREFINT_Factory_CONV byte represents the LSB of the V_{REFINT} 12-bit ADC conversion result. The MSB have a fixed value: 0x6.
3. The TS_Factory_CONV_V90 byte represents the LSB of the V₉₀ 12-bit ADC conversion result. The MSB

have a fixed value: 0x3.

4. Refer to [Table 9](#) for an overview of hardware register mapping, to [Table 8](#) for details on I/O port hardware registers, and to [Table 10](#) for information on CPU/SWIM/debug module controller registers.

Table 6. Flash and RAM boundary addresses

Memory area	Size	Start address	End address
RAM	2 Kbyte	0x00 0000	0x00 07FF
Flash program memory	16 Kbyte	0x00 8000	0x00 BFFF
	32 Kbyte	0x00 8000	0x00 FFFF

5.2 Register map

Table 7. Factory conversion registers

Address	Block	Register label	Register name	Reset status
0x00 4910	-	VREFINT_Factory_CONV ⁽¹⁾	Internal reference voltage factory conversion	0xXX
0x00 4911	-	TS_Factory_CONV_V90 ⁽²⁾	Temperature sensor output voltage	0xXX

1. The VREFINT_Factory_CONV byte represents the 8 LSB of the result of the VREFINT 12-bit ADC conversion performed in factory. The MSB have a fixed value: 0x6.
2. The TS_Factory_CONV_V90 byte represents the 8 LSB of the result of the V90 12-bit ADC conversion performed in factory. The 2 MSB have a fixed value: 0x3.

Table 8. I/O port hardware register map

Address	Block	Register label	Register name	Reset status
0x00 5000	Port A	PA_ODR	Port A data output latch register	0x00
0x00 5001		PA_IDR	Port A input pin value register	0xXX
0x00 5002		PA_DDR	Port A data direction register	0x00
0x00 5003		PA_CR1	Port A control register 1	0x01
0x00 5004		PA_CR2	Port A control register 2	0x00
0x00 5005	Port B	PB_ODR	Port B data output latch register	0x00
0x00 5006		PB_IDR	Port B input pin value register	0xXX
0x00 5007		PB_DDR	Port B data direction register	0x00
0x00 5008		PB_CR1	Port B control register 1	0x00
0x00 5009		PB_CR2	Port B control register 2	0x00

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5280	TIM3	TIM3_CR1	TIM3 control register 1	0x00
0x00 5281		TIM3_CR2	TIM3 control register 2	0x00
0x00 5282		TIM3_SMCR	TIM3 Slave mode control register	0x00
0x00 5283		TIM3_ETR	TIM3 external trigger register	0x00
0x00 5284		TIM3_DER	TIM3 DMA1 request enable register	0x00
0x00 5285		TIM3_IER	TIM3 interrupt enable register	0x00
0x00 5286		TIM3_SR1	TIM3 status register 1	0x00
0x00 5287		TIM3_SR2	TIM3 status register 2	0x00
0x00 5288		TIM3_EGR	TIM3 event generation register	0x00
0x00 5289		TIM3_CCMR1	TIM3 Capture/Compare mode register 1	0x00
0x00 528A		TIM3_CCMR2	TIM3 Capture/Compare mode register 2	0x00
0x00 528B		TIM3_CCER1	TIM3 Capture/Compare enable register 1	0x00
0x00 528C		TIM3_CNTRH	TIM3 counter high	0x00
0x00 528D		TIM3_CNTRL	TIM3 counter low	0x00
0x00 528E		TIM3_PSCR	TIM3 prescaler register	0x00
0x00 528F		TIM3_ARRH	TIM3 Auto-reload register high	0xFF
0x00 5290		TIM3_ARRL	TIM3 Auto-reload register low	0xFF
0x00 5291		TIM3_CCR1H	TIM3 Capture/Compare register 1 high	0x00
0x00 5292		TIM3_CCR1L	TIM3 Capture/Compare register 1 low	0x00
0x00 5293		TIM3_CCR2H	TIM3 Capture/Compare register 2 high	0x00
0x00 5294		TIM3_CCR2L	TIM3 Capture/Compare register 2 low	0x00
0x00 5295		TIM3_BKR	TIM3 break register	0x00
0x00 5296		TIM3_OISR	TIM3 output idle state register	0x00
0x00 5297 to 0x00 52AF	Reserved area (25 bytes)			

Table 21. Total current consumption in Wait mode (continued)

Symbol	Parameter	Conditions ⁽¹⁾	Typ	Max				Unit		
				55°C	85 °C ⁽²⁾	105 °C ⁽³⁾	125 °C ⁽⁴⁾			
I _{DD(Wait)}	Supply current in Wait mode	CPU not clocked, all peripherals OFF, code executed from Flash, V _{DD} from 1.65 V to 3.6 V	HSI	f _{CPU} = 125 kHz	0.38	0.48	0.49	0.50	0.56	mA
				f _{CPU} = 1 MHz	0.41	0.49	0.51	0.53	0.59	
				f _{CPU} = 4 MHz	0.50	0.57	0.58	0.62	0.66	
				f _{CPU} = 8 MHz	0.60	0.66	0.68	0.72	0.74	
				f _{CPU} = 16 MHz	0.79	0.84	0.86	0.87	0.90	
			HSE ⁽⁶⁾ external clock (f _{CPU} =HSE)	f _{CPU} = 125 kHz	0.06	0.08	0.09	0.10	0.12	
				f _{CPU} = 1 MHz	0.10	0.17	0.18	0.19	0.22	
				f _{CPU} = 4 MHz	0.24	0.36	0.39	0.41	0.44	
				f _{CPU} = 8 MHz	0.50	0.58	0.61	0.62	0.64	
			LSI	f _{CPU} = f _{LSI}	0.055	0.058	0.065	0.073	0.080	
				LSE ⁽⁸⁾ external clock (32.768 kHz)	f _{CPU} = f _{LSE}	0.051	0.056	0.060	0.065	

1. All peripherals OFF, V_{DD} from 1.65 V to 3.6 V, HSI internal RC osc., f_{CPU} = f_{SYSCLK}
2. For temperature range 6.
3. For temperature range 7.
4. For temperature range 3.
5. Flash is configured in I_{DDQ} mode in Wait mode by setting the EPM or WAITM bit in the Flash_CR1 register.
6. Oscillator bypassed (HSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the HSE consumption (I_{DD HSE}) must be added. Refer to [Table 37](#).
7. Tested in production.
8. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption (I_{DD HSE}) must be added. Refer to [Table 32](#).

Table 28. Current consumption under external reset

Symbol	Parameter	Conditions	Typ	Unit	
I _{DD(RST)}	Supply current under external reset ⁽¹⁾	All pins are externally tied to V _{DD}	V _{DD} = 1.8 V	48	μA
			V _{DD} = 3 V	76	
			V _{DD} = 3.6 V	91	

1. All pins except PA0, PB0 and PB4 are floating under reset. PA0, PB0 and PB4 are configured with pull-up under reset.

9.3.4 Clock and timing characteristics

HSE external clock (HSEBYP = 1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 29. HSE external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{HSE_ext}	External clock source frequency ⁽¹⁾		1	-	16	MHz
V _{HSEH}	OSC_IN input pin high level voltage	-	0.7 x V _{DD}	-	V _{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage		V _{SS}	-	0.3 x V _{DD}	
C _{in(HSE)}	OSC_IN input capacitance ⁽¹⁾	-	-	2.6	-	pF
I _{LEAK_HSE}	OSC_IN input leakage current	V _{SS} < V _{IN} < V _{DD}	-	-	±1	μA

1. Data guaranteed by design.

LSE external clock (LSEBYP=1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 30. LSE external clock characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f _{LSE_ext}	External clock source frequency ⁽¹⁾	-	32.768	-	kHz
V _{LSEH} ⁽²⁾	OSC32_IN input pin high level voltage	0.7 x V _{DD}	-	V _{DD}	V
V _{LSEL} ⁽²⁾	OSC32_IN input pin low level voltage	V _{SS}	-	0.3 x V _{DD}	
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾	-	0.6	-	pF
I _{LEAK_LSE}	OSC32_IN input leakage current	-	-	±1	μA

1. Data guaranteed by design.

2. Data based on characterization results.

HSE oscillator critical g_m formula

$$g_{m\text{crit}} = (2 \times \Pi \times f_{\text{HSE}})^2 \times R_m (2C_o + C)^2$$

R_m : Motional resistance (see crystal specification), L_m : Motional inductance (see crystal specification),
 C_m : Motional capacitance (see crystal specification), C_o : Shunt capacitance (see crystal specification),
 $C_{L1}=C_{L2}=C$: Grounded external capacitance
 $g_m \gg g_{m\text{crit}}$

LSE crystal/ceramic resonator oscillator

The LSE clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 32. LSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE}	Low speed external oscillator frequency	-	-	32.768	-	kHz
R_F	Feedback resistor	$\Delta V = 200 \text{ mV}$	-	1.2	-	M Ω
$C^{(1)}$	Recommended load capacitance ⁽²⁾	-	-	8	-	pF
$I_{\text{DD(LSE)}}$	LSE oscillator power consumption	-	-	-	1.4 ⁽³⁾	μA
		$V_{\text{DD}} = 1.8 \text{ V}$	-	450	-	nA
		$V_{\text{DD}} = 3 \text{ V}$	-	600	-	
		$V_{\text{DD}} = 3.6 \text{ V}$	-	750	-	
g_m	Oscillator transconductance	-	3 ⁽³⁾	-	-	$\mu\text{A/V}$
$t_{\text{SU(LSE)}}^{(4)}$	Startup time	V_{DD} is stabilized	-	1	-	s

1. $C=C_{L1}=C_{L2}$ is approximately equivalent to 2 x crystal C_{LOAD} .
2. The oscillator selection can be optimized in terms of supply current using a high quality resonator with a small R_m value. Refer to crystal manufacturer for more details.
3. Data guaranteed by design.
4. $t_{\text{SU(LSE)}}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 39. Output driving current (high sink ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
High sink	$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +2 \text{ mA}$, $V_{DD} = 3.0 \text{ V}$	-	0.45	V
			$I_{IO} = +2 \text{ mA}$, $V_{DD} = 1.8 \text{ V}$	-	0.45	V
			$I_{IO} = +10 \text{ mA}$, $V_{DD} = 3.0 \text{ V}$	-	0.7	V
	$V_{OH}^{(2)}$	Output high level voltage for an I/O pin	$I_{IO} = -2 \text{ mA}$, $V_{DD} = 3.0 \text{ V}$	$V_{DD}-0.45$	-	V
			$I_{IO} = -1 \text{ mA}$, $V_{DD} = 1.8 \text{ V}$	$V_{DD}-0.45$	-	V
			$I_{IO} = -10 \text{ mA}$, $V_{DD} = 3.0 \text{ V}$	$V_{DD}-0.7$	-	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in [Table 16](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in [Table 16](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .

Table 40. Output driving current (true open drain ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Open drain	$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +3 \text{ mA}$, $V_{DD} = 3.0 \text{ V}$	-	0.45	V
			$I_{IO} = +1 \text{ mA}$, $V_{DD} = 1.8 \text{ V}$	-	0.45	

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in [Table 16](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .

Table 41. Output driving current (PA0 with high sink LED driver capability)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
\bar{R}	$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +20 \text{ mA}$, $V_{DD} = 2.0 \text{ V}$	-	0.45	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in [Table 16](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .

In the following table, data is based on characterization results, not tested in production.

Table 51. DAC accuracy

Symbol	Parameter	Conditions	Typ	Max	Unit
DNL	Differential non linearity ⁽¹⁾	$R_L \geq 5 \text{ k}\Omega, C_L \leq 50 \text{ pF}$ DACOUT buffer ON ⁽²⁾	1.5	3	12-bit LSB
		No load DACOUT buffer OFF	1.5	3	
INL	Integral non linearity ⁽³⁾	$R_L \geq 5 \text{ k}\Omega, C_L \leq 50 \text{ pF}$ DACOUT buffer ON ⁽²⁾	2	4	
		No load DACOUT buffer OFF	2	4	
Offset	Offset error ⁽⁴⁾	$R_L \geq 5 \text{ k}\Omega, C_L \leq 50 \text{ pF}$ DACOUT buffer ON ⁽²⁾	± 10	± 25	
		No load DACOUT buffer OFF	± 5	± 8	
Offset1	Offset error at Code 1 ⁽⁵⁾	DACOUT buffer OFF	± 1.5	± 5	
Gain error	Gain error ⁽⁶⁾	$R_L \geq 5 \text{ k}\Omega, C_L \leq 50 \text{ pF}$ DACOUT buffer ON ⁽²⁾	+0.1/-0.2	+0.2/-0.5	%
		No load DACOUT buffer OFF	+0/-0.2	+0/-0.4	
TUE	Total unadjusted error	$R_L \geq 5 \text{ k}\Omega, C_L \leq 50 \text{ pF}$ DACOUT buffer ON ⁽²⁾	12	30	12-bit LSB
		No load DACOUT buffer OFF	8	12	

1. Difference between two consecutive codes - 1 LSB.
2. For 48-pin packages only. For 28-pin and 32-pin packages, DAC output buffer must be kept off and no load must be applied.
3. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023.
4. Difference between the value measured at Code (0x800) and the ideal value = $V_{REF+}/2$.
5. Difference between the value measured at Code (0x001) and the ideal value.
6. Difference between the ideal slope of the transfer function and the measured slope computed from Code 0x000 and 0xFFFF when buffer is ON, and from Code giving 0.2 V and ($V_{DDA} - 0.2$) V when buffer is OFF.

In the following table, data is guaranteed by design, not tested in production.

Table 52. DAC output on PB4-PB5-PB6⁽¹⁾

Symbol	Parameter	Conditions	Max	Unit
R_{int}	Internal resistance between DAC output and PB4-PB5-PB6 output	$2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	1.4	k Ω
		$2.4 \text{ V} < V_{DD} < 3.6 \text{ V}$	1.6	
		$2.0 \text{ V} < V_{DD} < 3.6 \text{ V}$	3.2	
		$1.8 \text{ V} < V_{DD} < 3.6 \text{ V}$	8.2	

1. 32 or 28-pin packages only. The DAC channel can be routed either on PB4, PB5 or PB6 using the routing interface I/O switch registers.

Table 59. EMI data ⁽¹⁾

Symbol	Parameter	Conditions	Monitored frequency band	Max vs.	Unit
				16 MHz	
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = +25 °C, LQFP32 conforming to IEC61967-2	0.1 MHz to 30 MHz	-3	dBμV
			30 MHz to 130 MHz	9	
			130 MHz to 1 GHz	4	
			SAE EMI Level	2	-

1. Not tested in production.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and charge device model. This test conforms to the JESD22-A114A/A115A standard.

Table 60. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)		500	

1. Data based on characterization results.

Static latch-up

- **LU:** 3 complementary static tests are required on 6 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Table 61. Electrical sensitivities

Symbol	Parameter	Class
LU	Static latch-up class	II

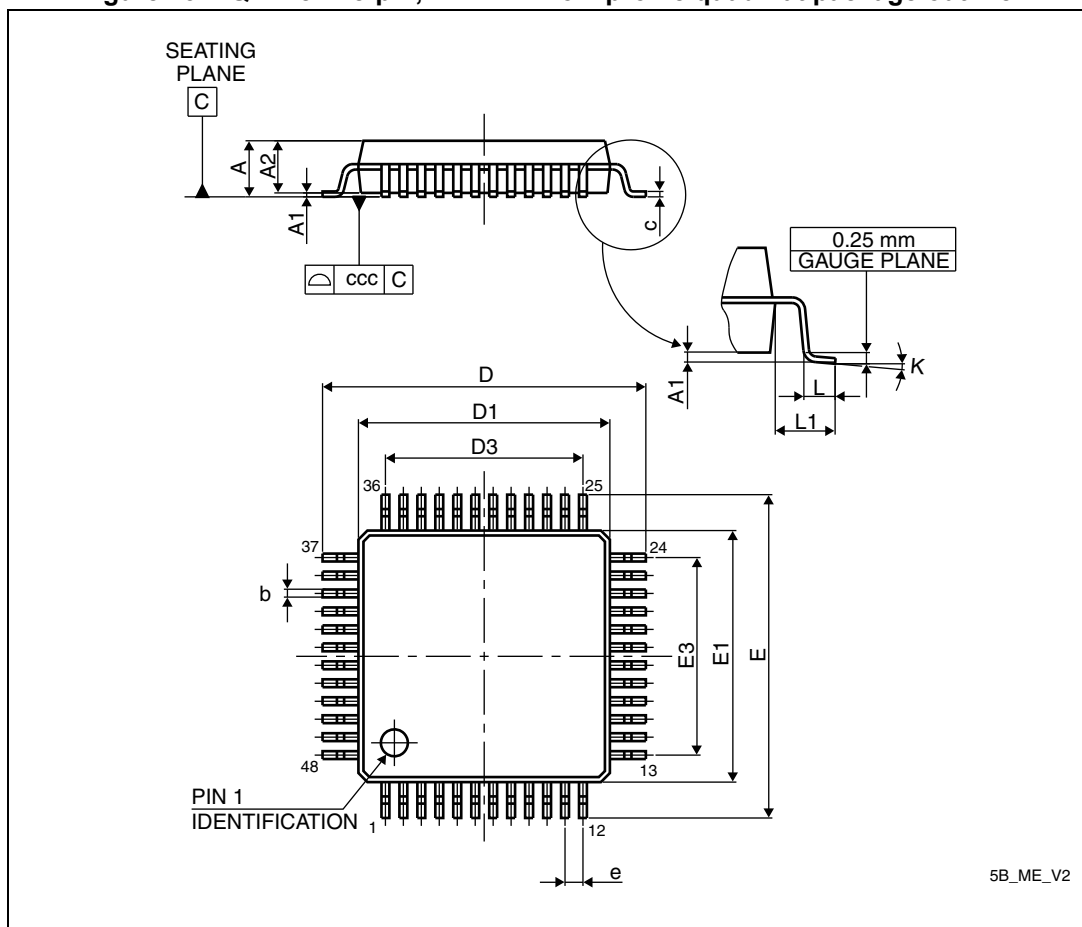
10 Package information

10.1 ECOPACK

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

10.2 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

10.3 UFQFPN48 package information

Figure 46. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline



A0B9_ME_V3

1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Table 63. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

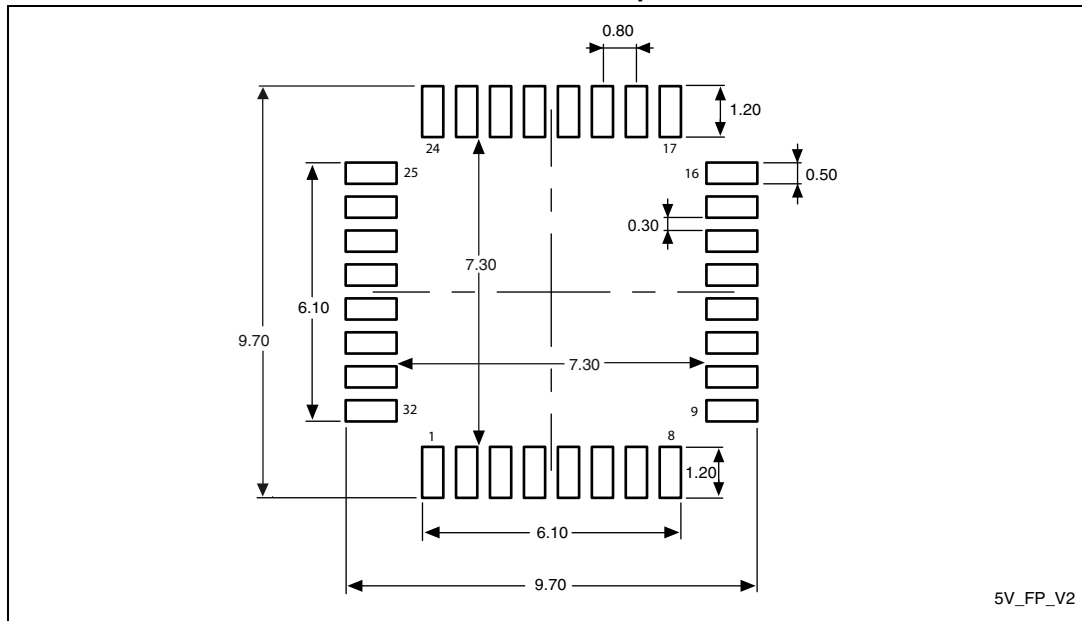
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 47. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Figure 50. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package recommended footprint

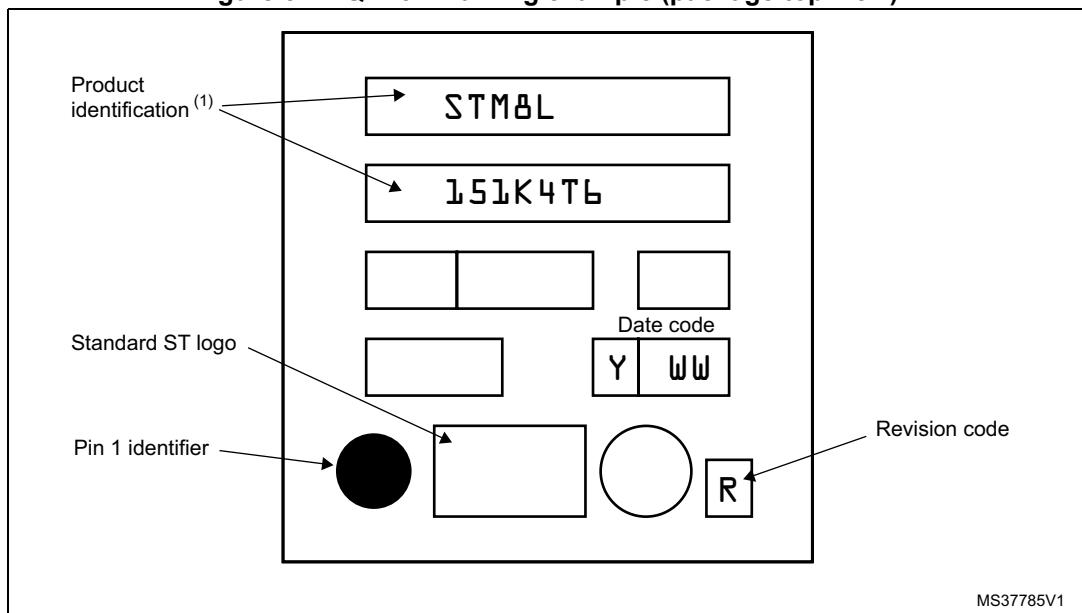


1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location. Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 51. LQFP32 marking example (package top view)



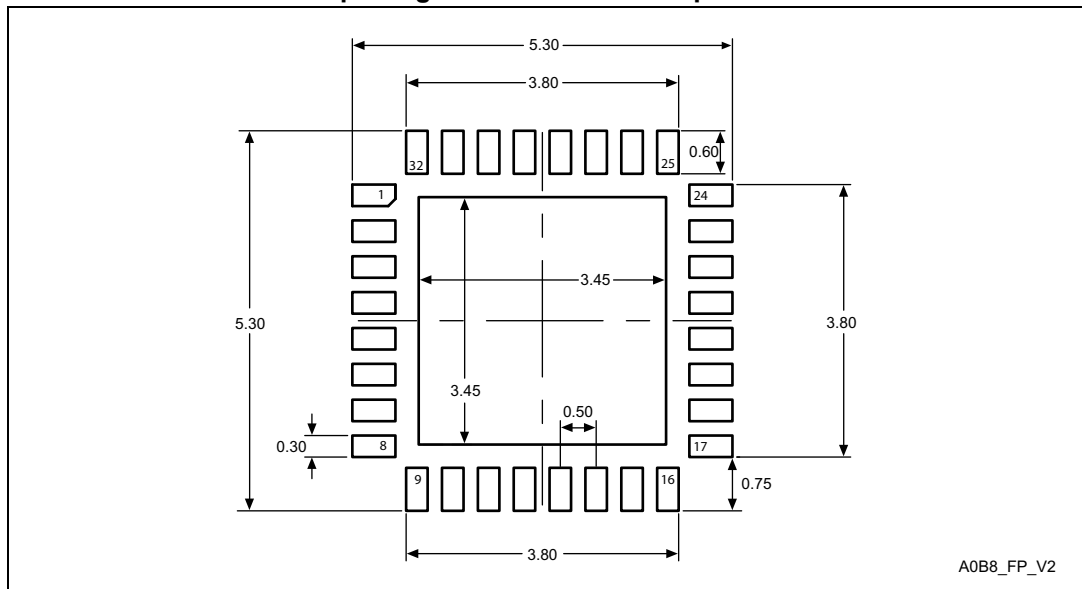
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering

Table 65. UFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. UFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

12 Revision history

Table 69. Document revision history

Date	Revision	Changes
06-Aug-2009	1	Initial release
10-Sep-2009	2	<p>Updated peripheral naming throughout document. Added <i>Figure: STM8L151Cx 48-pin pinout (without LCD)</i>. Added capacitive sensing channels in <i>Features</i>. Updated PA7, PC0 and PC1 in <i>Table: Medium density STM8L15x pin description</i>. Changed CLK and REMAP register names. Changed description of WDGHALT. Added typical power consumption values in <i>Table 18</i> to <i>Table 26</i>. Corrected VIH max value.</p>
11-Dec-2009	3	<p>Added WLCSP28 package Modified <i>Figure: Memory map</i> and added 2 notes. Modified Low power run mode in <i>Section: Low power modes</i>. Added <i>Section: Unique ID</i>. Modified <i>Table: Interrupt mapping</i> (added reserved area at address 0x00 8008) Modified OPT4 option bits in <i>Table: Option byte addresses</i>. <i>Table: Option byte description</i>: modified OPT0 description (“disable” instead of “enable”) and OPT1 description Added OPTBL option bytes Modified <i>Section: Electrical parameters</i>.</p>
02-Apr-2010	4	<p>Changed title of the document (STM8L151x4, STM8L151x6, STM8L152x4, STM8L152x6) Changed pinout (V_{SS1}, V_{DD1}, V_{SS2}, V_{DD2} instead of V_{SS}, V_{DD}, V_{SSIO}, V_{DDIO}) Changed packages Changed first page Modified note 1 in <i>Table: Medium density STM8L15x pin description</i>. Added note to PA7, PC0, PC1 and PE0 in <i>Table: Medium density STM8L15x pin description</i>. Modified <i>Figure: Memory map</i>. Modified <i>Table: WLCSP28 – 28-pin wafer level chip scale package, package mechanical data</i> (min and max columns swapped) Modified <i>Figure: WLCSP28 – 28-pin wafer level chip scale package, package outline</i> (A1 ball location) Renamed Rm, Lm and Cm EXTI_CONF replaced with EXTI_CONF1 in <i>Table: General hardware register map</i>. Updated <i>Section: Electrical parameters</i>.</p>

Table 69. Document revision history (continued)

Date	Revision	Changes
10-Feb-2012	8	<p><i>Features:</i> replaced “Dynamic consumption’ with ‘Consumption’.</p> <p><i>Table: Medium density STM8L15x pin description:</i> updated OD column of NRST/PA1 pin.</p> <p><i>Table: Interrupt mapping:</i> removed tamper 1, tamper 2 and tamper 3.</p> <p><i>Figure: UFQFPN48 package outline:</i> replaced.</p> <p><i>Table: UFQFPN48 package mechanical data:</i> updated title.</p> <p><i>Figure: UFQFPN32 - 32-lead ultra thin fine pitch quad flat no-lead package outline (5 x 5):</i> removed the line over A1.</p> <p><i>Figure: UFQFPN28 package outline:</i> replaced to improve readability of UFQFPN28 package dimensions A, L, and L1.</p> <p><i>Figure: Recommended UFQFPN28 footprint (dimensions in mm):</i> updated title.</p> <p><i>Figure: WLCSP28 package outline:</i> updated title.</p> <p><i>Table: WLCSP28 package mechanical data:</i> updated title.</p>
02-Mar-2012	9	<p>Updated <i>Table: UFQFPN48 package mechanical data.</i></p> <p>Updated <i>Figure: UFQFPN28 package outline, Figure: Recommended UFQFPN28 footprint (dimensions in mm)</i> and <i>Table: UFQFPN28 package mechanical data.</i></p> <p><i>Table: WLCSP28 package mechanical data:</i> Min and Max values removed for e1, e2, e3, e4, F and G dimensions.</p>
30-Mar-2012	10	<p><i>Figure: SPI1 timing diagram - master mode(1):</i> changed SCK signals to ‘output’ instead of ‘input’.</p> <p><i>Figure: Medium density STM8L15x ordering information scheme:</i> added ‘Tape & reel’ to package section.</p>
26-Apr-2012	11	<p>Updated <i>Table: WLCSP28 package mechanical data.</i></p>
12-Nov-2013	12	<p>Updated <i>Table: WLCSP28 package mechanical data.</i></p> <p>Updated <i>Table: Medium-density STM8L15x pin description.</i></p> <p>Updated <i>Table 2: Medium density STM8L15x low power device features and peripheral counts.</i></p> <p>Added <i>Figure: Recommended LQFP48 footprint</i> and <i>Figure: Recommended LQFP32 footprint.</i></p>
12-Aug-2013	13	<p>Changed the default setting value of OPT5 to 0x00 in <i>Table: Option byte addresses.</i></p> <p>Added tTEMP ‘BOR detector enabled’ and ‘disabled’ characteristics in <i>Table: Embedded reset and power control block characteristics.</i></p> <p>Updated E2, D2 and ddd in <i>Table: UFQFPN48 package mechanical data</i></p>